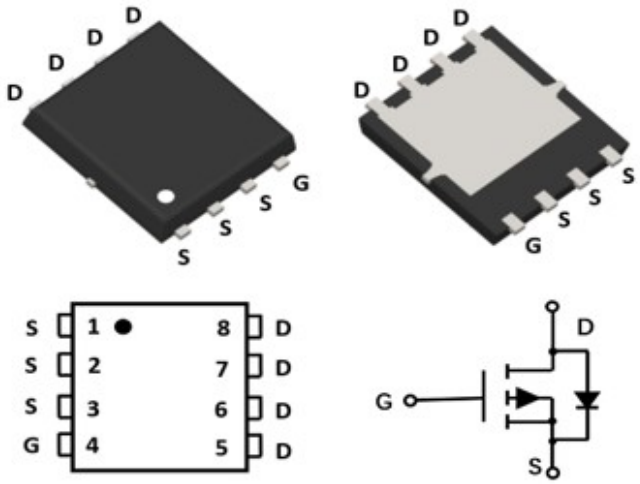
P-Channel Enhancement Mode Field Effect Transistor

PDFN 5X6



Product Summary

- V_{DS} -100V
- I_D -25A
- $R_{DS(ON)}$(at V_{GS}=-10V) ＜48 mohm
- $R_{DS(ON)}$(at V_{GS}=-4.5V) ＜55 mohm
- 100% UIS Tested
- 100% ▽V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	Tc=25℃	I_D	-25	A
	Tc=100℃		-16	
Pulsed Drain Current [A]		I_{DM}	-100	A
Avalanche energy [B]		E_{AS}	162	mJ
Total Power Dissipation	Tc=25℃	P_D	72	W
	Tc=100℃		28.8	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

■Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient [D]	t≤10S	$R_{\theta JA}$	15	20	℃/W
Thermal Resistance Junction-to-Ambient [D]	Steady-State		40	50	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.35	1.7	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG25GP10A	F1	YJG25GP10A	5000	10000	100000	13“ reel

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions		Min	Typ	Max	Units
Static Parameter							
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=-250μA		-100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-100V,V_{GS}=0V	T_J=25℃			-1	μA
			T_J=55℃			-5	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V				±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=-250μA		-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= -10V, I_D=-15A			38	48	mΩ
		V_{GS}= -4.5V, I_D=-7A			43	55	
Diode Forward Voltage	V_{SD}	I_S=-15A,V_{GS}=0V				-1.3	V
Maximum Body-Diode Continuous Current	I_S					-25	A
Dynamic Parameters							
Input Capacitance	C_{iss}	V_{DS}=-50V,V_{GS}=0V,f=1MHZ			2100		pF
Output Capacitance	C_{oss}				236		
Reverse Transfer Capacitance	C_{rss}				48		
Switching Parameters							
Total Gate Charge	$Q_{g(-10V)}$	V_{GS}=-10V,V_{DS}=-50V,I_D=-5A			40		nC
Total Gate Charge	$Q_{g(-4.5V)}$				19.4		
Gate-Source Charge	Q_{gs}				7.8		
Gate-Drain Charge	Q_{gd}				8.6		
Reverse Recovery Chrage	Q_{rr}	I_F=-5A, di/dt=100A/us			280		
Reverse Recovery Time	t_{rr}				104		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=-10V,V_{DD}=-50V,I_{DS}=-5A R_{GEN}=6Ω			13		
Turn-on Rise Time	t_r				39		
Turn-off Delay Time	$t_{D(off)}$				100.1		
Turn-off fall Time	t_f				105.3		

A. Repetitive rating; pulse width limited by max. junction temperature.
B. V_{DD}=50V, R_G=25Ω, L=0.5mH.
C. Pd is based on max. junction temperature, using junction-case thermal resistance.
D. The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA =25° C. The Power dissipation PDSM is based on RθJA t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design

■ Typical Performance Characteristics

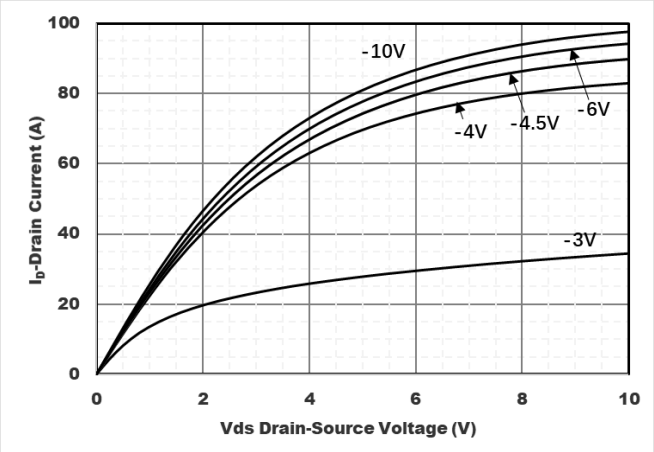


Figure1. Output Characteristics

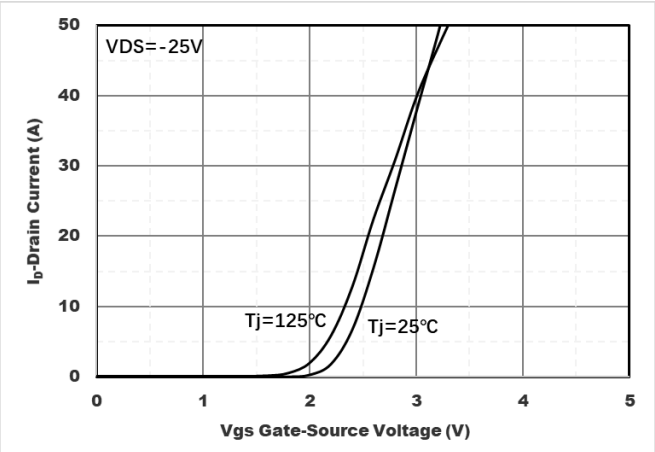


Figure2. Transfer Characteristics

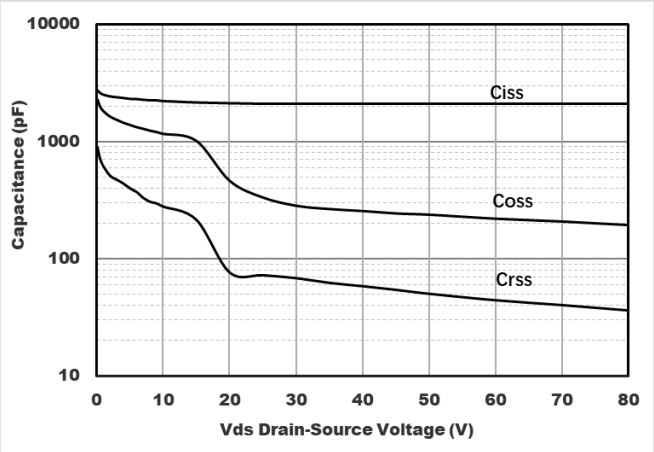


Figure3. Capacitance Characteristics

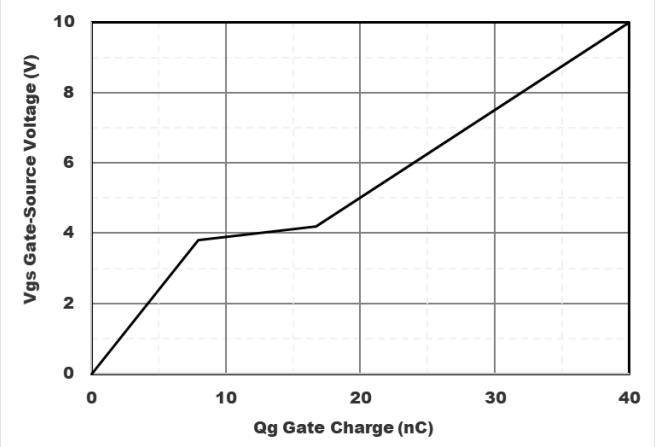


Figure4. Gate Charge

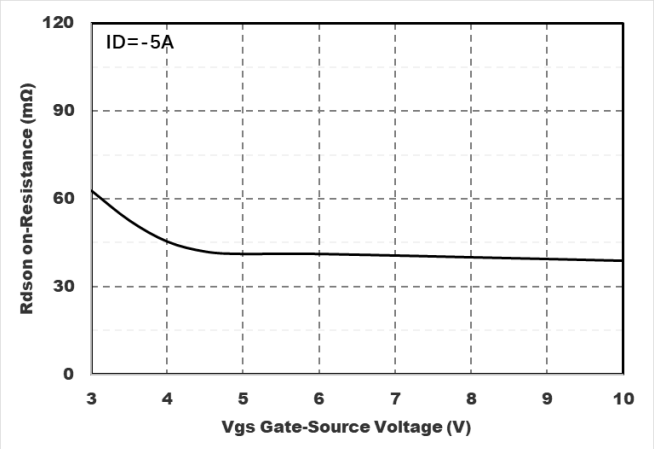


Figure5. : On-Resistance vs. Gate to Source Voltage

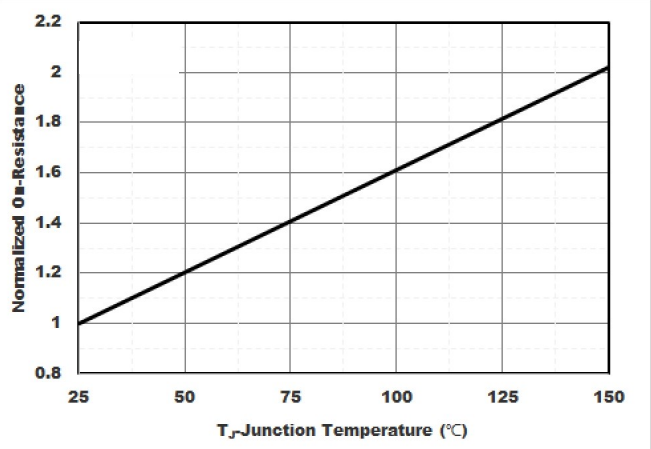


Figure6.Normalized On-Resistance

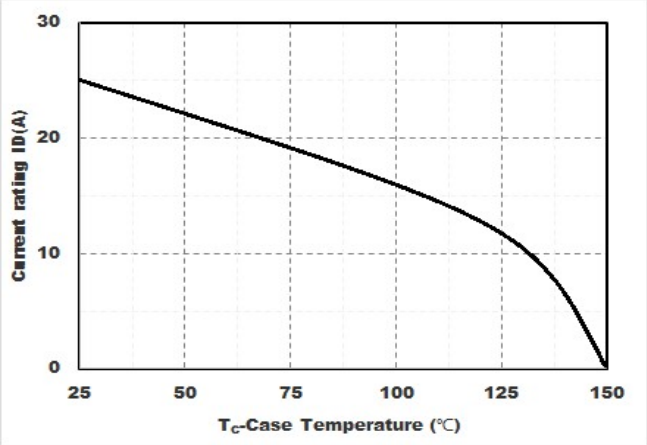


Figure7. Drain current

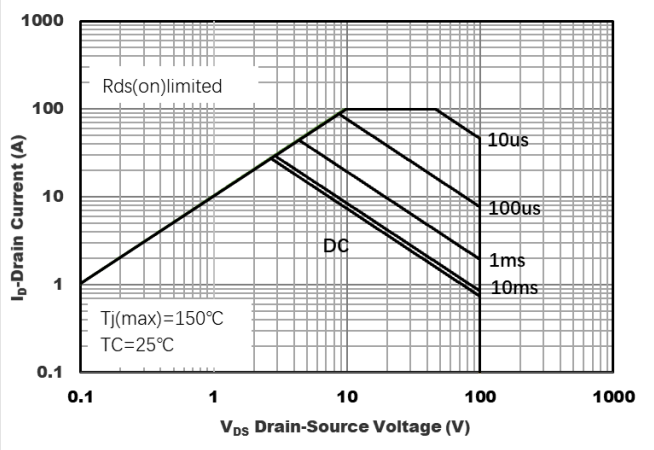


Figure8.Safe Operation Area

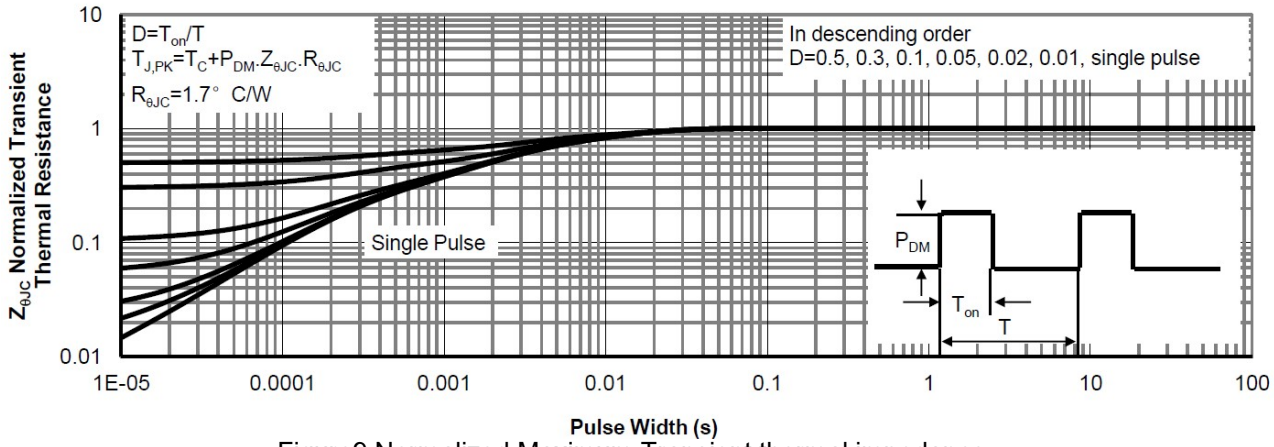
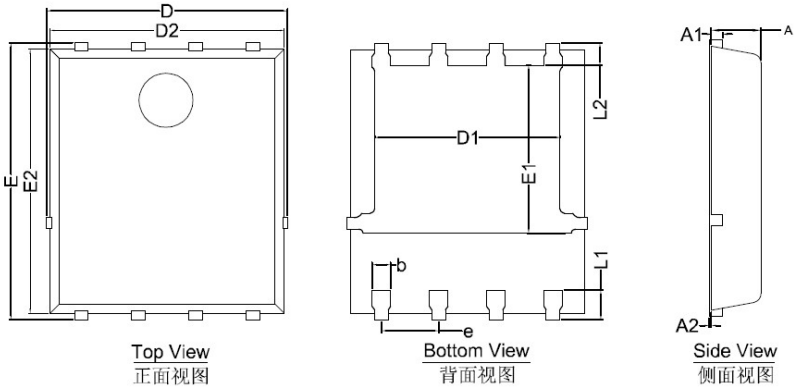
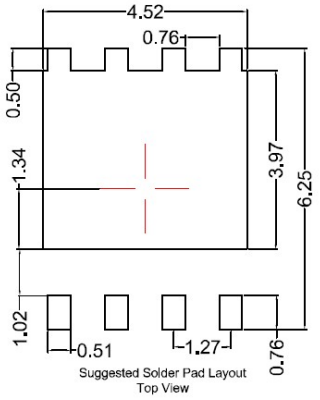


Figure9.Normalized Maximum Transient thermal impedance

■ PDFN5x6 Package information





Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1		0.254 BSC	
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2		0.50 BSC	
b	0.31	0.41	0.51
e		1.27 BSC	

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